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(54) **SEMICONDUCTOR STRUCTURE WITH  
BACKSIDE THROUGH SILICON VIAS AND  
METHOD OF OBTAINING DIE IDS  
THEREOF**

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**ABSTRACT**

A semiconductor structure with backside through silicon vias (TSVs) is provided in the present invention, including a semiconductor substrate with a front side and a back side, multiple dummy pads set on the front side, multiple backside TSVs extending from the back side to the front side, wherein a number of the dummy pads are connected with the backside TSVs while other dummy pads are not connected with the backside TSVs, and a metal coating covering the back side and the surface of backside TSVs and connected with those dummy pads that connecting with the backside TSVs.

